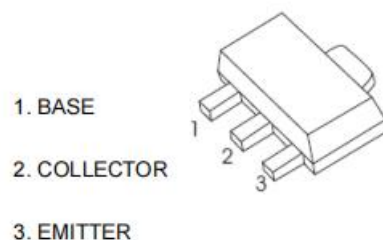


## SOT-89-3L Bipolar Transistor 双极型三极管

### ■ Features 特点

PNP Low Saturation Voltage 低饱和压降

### ■ Absolute Maximum Ratings 最大额定值



| Characteristic 特性参数                         | Symbol 符号                     | Rat 额定值                      | Unit 单位                     |
|---------------------------------------------|-------------------------------|------------------------------|-----------------------------|
| Collector-Base Voltage 集电极基极电压              | $V_{CBO}$                     | -40                          | V                           |
| Collector-Emitter Voltage 集电极发射极电压          | $V_{CEO}$                     | -30                          | V                           |
| Emitter-Base Voltage 发射极基极电压                | $V_{EBO}$                     | -6                           | V                           |
| Collector Current 集电极电流                     | $I_C$                         | -3000                        | mA                          |
| Power dissipation 耗散功率                      | $P_C(T_a=25^{\circ}\text{C})$ | 500                          | mW                          |
| Thermal Resistance Junction-Ambient 热阻      | $R_{\theta JA}$               | 250                          | $^{\circ}\text{C}/\text{W}$ |
| Junction and Storage Temperature<br>结温和储藏温度 | $T_J, T_{stg}$                | -55to+150 $^{\circ}\text{C}$ |                             |

### ■ Device Marking 产品打标

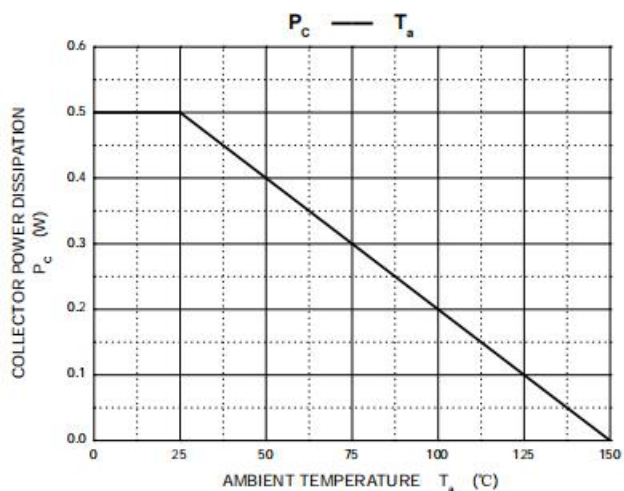
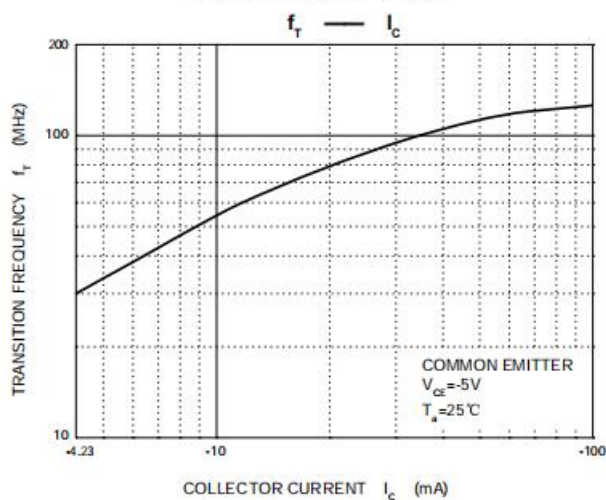
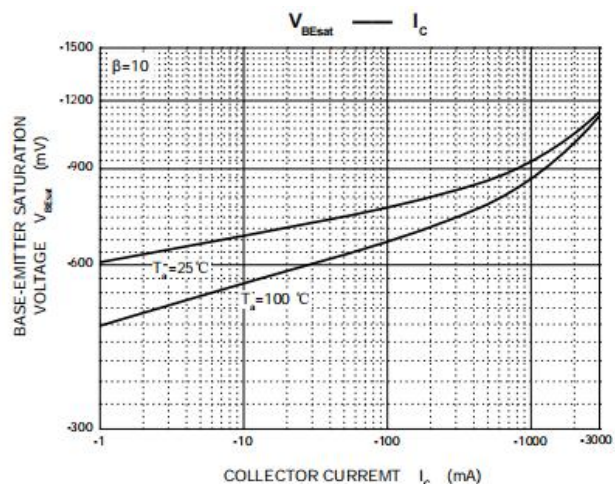
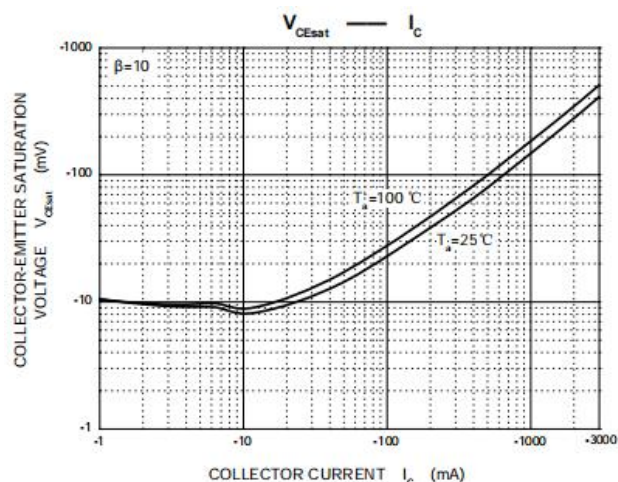
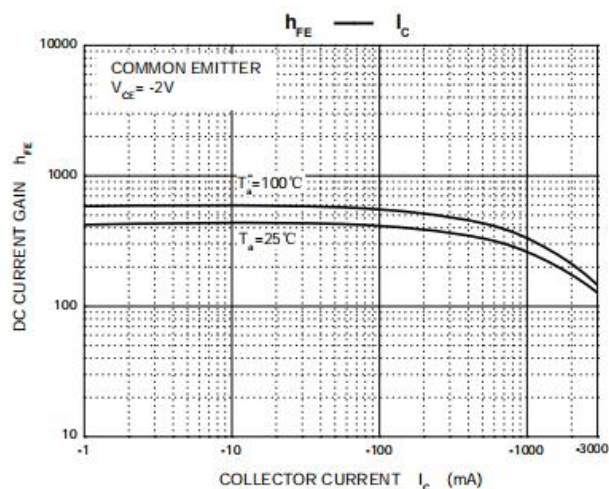
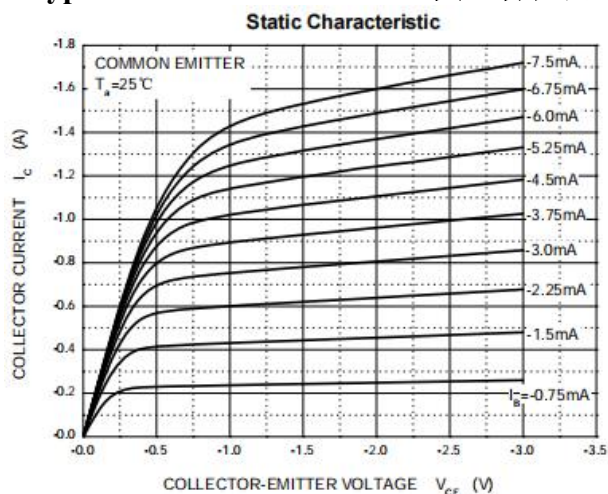
|          |           |            |            |             |
|----------|-----------|------------|------------|-------------|
| $H_{FE}$ | 60-120(R) | 100-200(O) | 160-320(Y) | 200-400(GR) |
| Mark     | B772      |            |            |             |

## ■Electrical Characteristics 电特性

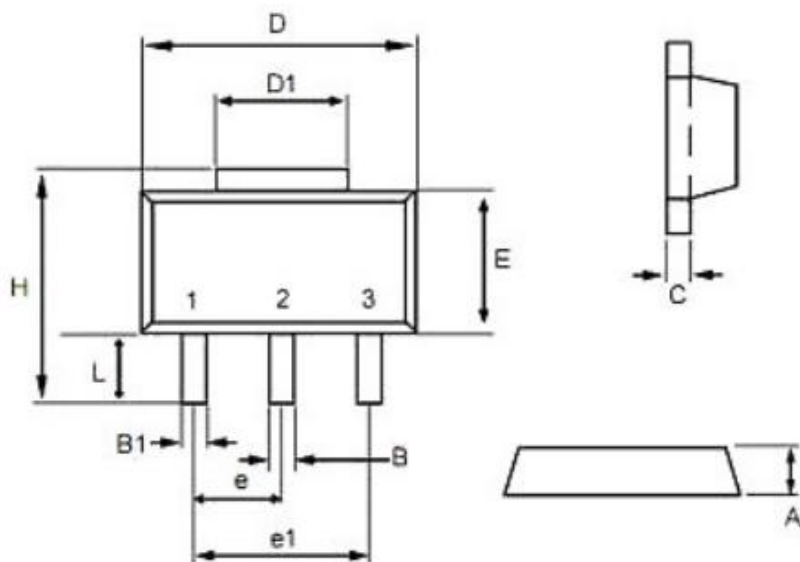
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

| Characteristic<br>特性参数                                                                          | Symbol<br>符号  | Min<br>最小值 | Type<br>典型值 | Max<br>最大值 | Unit<br>单位    |
|-------------------------------------------------------------------------------------------------|---------------|------------|-------------|------------|---------------|
| Collector-Base Breakdown Voltage<br>集电极基极击穿电压( $I_C = -100\mu\text{A}$ , $I_E = 0$ )            | $BV_{CBO}$    | -40        | —           | —          | V             |
| Collector-Emitter Breakdown Voltage<br>集电极发射极击穿电压( $I_C = -10\text{mA}$ , $I_B = 0$ )           | $BV_{CEO}$    | -30        | —           | —          | V             |
| Emitter-Base Breakdown Voltage<br>发射极基极击穿电压( $I_E = -100\mu\text{A}$ , $I_C = 0$ )              | $BV_{EBO}$    | -6         | —           | —          | V             |
| Collector-Base Leakage Current<br>集电极基极漏电流( $V_{CB} = -40\text{V}$ , $I_E = 0$ )                | $I_{CBO}$     | —          | —           | -1         | $\mu\text{A}$ |
| Collector-Emitter Leakage Current<br>集电极发射极漏电流( $V_{CE} = -30\text{V}$ , $I_B = 0$ )            | $I_{CEO}$     | —          | —           | -10        | $\mu\text{A}$ |
| Emitter-Base Leakage Current<br>发射极基极漏电流( $V_{EB} = -6\text{V}$ , $I_C = 0$ )                   | $I_{EBO}$     | —          | —           | -1         | $\mu\text{A}$ |
| DC Current Gain<br>直流电流增益( $V_{CE} = -2\text{V}$ , $I_C = -1000\text{mA}$ )                     | $H_{FE}$      | 60         | —           | 400        |               |
| Collector-Emitter Saturation Voltage<br>集电极发射极饱和压降( $I_C = -2\text{A}$ , $I_B = -0.2\text{A}$ ) | $V_{CE(sat)}$ | —          | —           | -0.5       | V             |
| Base-Emitter Saturation Voltage<br>基极发射极饱和压降( $I_C = -2\text{A}$ , $I_B = -0.2\text{A}$ )       | $V_{BE(sat)}$ | —          | —           | -1.5       | V             |
| Transition Frequency<br>特征频率( $V_{CE} = -5\text{V}$ , $I_C = -100\text{mA}$ )                   | $f_T$         | —          | 80          | —          | MHz           |
| Output Capacitance<br>输出电容( $V_{CB} = -10\text{V}$ , $I_E = 0$ , $f = 1\text{MHz}$ )            | $C_{ob}$      | —          | 35          | —          | pF            |

## ■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



| Symbol | Dimensions In Millimeters |      | Dimensions In Inches |       |
|--------|---------------------------|------|----------------------|-------|
|        | Min                       | Max  | Min                  | Max   |
| A      | 1.40                      | 1.60 | 0.055                | 0.063 |
| B      | 0.40                      | 0.56 | 0.016                | 0.022 |
| B1     | 0.35                      | 0.48 | 0.014                | 0.019 |
| C      | 0.35                      | 0.44 | 0.014                | 0.017 |
| D      | 4.40                      | 4.60 | 0.173                | 0.181 |
| D1     | 1.35                      | 1.83 | 0.053                | 0.072 |
| e      | 1.45                      | 1.55 | 0.057                | 0.061 |
| e1     | 2.95                      | 3.05 | 0.116                | 0.120 |
| E      | 2.29                      | 2.60 | 0.090                | 0.102 |
| H      | 3.75                      | 4.25 | 0.148                | 0.167 |
| L      | 0.80                      | 1.20 | 0.031                | 0.047 |